

Title (en)  
THERMAL PRINT HEAD CONTAINING SUPER-THIN POLYCRYSTALLINE SILICON FILM TRANSISTOR

Publication  
**EP 0235827 A3 19891227 (EN)**

Application  
**EP 87103260 A 19870306**

Priority  
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Abstract (en)  
[origin: EP0235827A2] Disclosed is herein a thermal print head containing super-thin polycrystalline silicon film transistors, comprising: heating resistors (3B, 2I) formed in a thin polycrystalline silicon layer (3) formed over a substrate (I); and a driving circuit comprising super-thin film transistors (4, 5, 6) each having a thin active layer (3c), formed in the polycrystalline silicon layer (3).

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**B41J 3/20**

IPC 8 full level  
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**B41J 2/315** (2013.01 - KR); **B41J 2/33515** (2013.01 - EP); **B41J 2/33545** (2013.01 - EP); **B41J 2/3355** (2013.01 - EP);  
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Citation (search report)  
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• [A] US 4472875 A 19840925 - CHRISTIAN RAYMOND R [US], et al  
• [A] PATENT ABSTRACTS OF JAPAN, vol. 7, no. 59 (M-199)(1204) 11 March 1983; & JP-A-57 203 573 (FUJI XEROX K.K.) 13-12-1982  
• [AD] PATENT ABSTRACTS OF JAPAN, vol. 7, no. 275 (M-261)(1420) 8 December 1983; & JP-A-58 153 672 (NIPPON DENSHIN DENWA KOSHA) 12-09-1983

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US11225086B2

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